

# **Phase Control Thyristor**



DS5822-4 February 2014 (LN31296)

### **FEATURES**

- Double Side Cooling
- High Surge Capability

### **APPLICATIONS**

- High Power Drives
- High Voltage Power Supplies
- Static Switches

#### **VOLTAGE RATINGS**

Part and Ordering Number	Repetitive Peak Voltages V <sub>DRM</sub> and V <sub>RRM</sub> V	Conditions
DCR3480B52* DCR3480B50 DCR3480B48 DCR3480B46	5200 5000 4800 4600	$\begin{split} T_{vj} &= \text{-}40^{\circ}\text{C to 125}^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 300\text{mA}, \\ V_{DRM}, V_{RRM}  t_p &= 10\text{ms}, \\ V_{DSM}  \&  V_{RSM} &= \\ V_{DRM}  \&  V_{RRM}  + 100V \\ respectively \end{split}$

Lower voltage grades available. \*5000V @ -40°C, 5200V @ 0°C

## **ORDERING INFORMATION**

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR3480B52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

### **KEY PARAMETERS**

$V_{DRM}$	5200V
$I_{T(AV)}$	3430A
I <sub>TSM</sub>	49000A
dV/dt*	1500V/µs
dl/dt	400A/μs

\* Higher dV/dt selections available

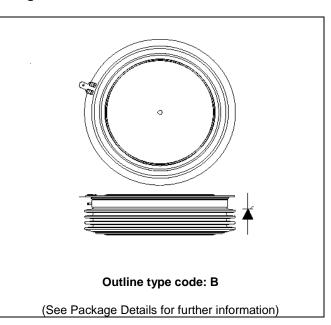


Fig. 1 Package outline





## **CURRENT RATINGS**

## $T_{\text{case}}$ = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I <sub>T(AV)</sub> Mean on-state current		Half wave resistive load	3430	А
I <sub>T(RMS)</sub> RMS value		-	5388	Α
I <sub>T</sub> Continuous (direct) on-state current		-	4890	А

## **SURGE RATINGS**

Symbol Parameter		Test Conditions	Max.	Units
I <sub>TSM</sub>	Surge (non-repetitive) on-state current	10ms half sine, T <sub>case</sub> = 125°C	49.0	kA
I <sup>2</sup> t I <sup>2</sup> t for fusing		$V_R = 0$	12.0	MA <sup>2</sup> s

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	s	Min.	Max.	Units
R <sub>th(j-c)</sub>	Thermal resistance – junction to case	Double side cooled	DC	-	0.007	°C/W
		Single side cooled	Anode DC	-	0.0116	°C/W
			Cathode DC	-	0.0181	°C/W
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink	Clamping force 76kN Double side		-	0.0014	°C/W
		(with mounting compound)	Single side	-	0.0028	°C/W
$T_{vj}$	Virtual junction temperature	Blocking V <sub>DRM</sub> / V <sub>RRM</sub>		-	125	°C
T <sub>stg</sub>	Storage temperature range			-55	125	°C
F <sub>m</sub>	Clamping force			68.0	84.0	kN





# **DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditio	Test Conditions		Max.	Units
I <sub>RRM</sub> /I <sub>DRM</sub>	Peak reverse and off-state current	At V <sub>RRM</sub> /V <sub>DRM</sub> , T <sub>case</sub> = 125°C		-	300	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125$ °C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V <sub>DRM</sub> to 2x I <sub>T(AV)</sub>	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, $10\Omega$ , $t_r < 0.5\mu s$ , $T_j = 125^{\circ}C$	Non-repetitive	-	400	A/µs
V <sub>T(TO)</sub>	Threshold voltage – Low level	500A to 2400A at T <sub>case</sub> = 125	5°C	-	0.86	V
	Threshold voltage – High level	2400A to 7200A at T <sub>case</sub> = 12	25°C	-	0.98	V
r <sub>T</sub>	On-state slope resistance – Low level	500A to 2400A at T <sub>case</sub> = 125°C		-	0.2533	mΩ
	On-state slope resistance – High level	2400A to 7200A at T <sub>case</sub> = 125°C		-	0.1886	mΩ
t <sub>gd</sub>	Delay time	$V_D = 67\% \ V_{DRM}$ , gate source 30V, $10\Omega$ $t_r = 0.5 \mu s$ , $T_j = 25^{\circ} C$		-	3	μs
t <sub>q</sub>	Turn-off time	$T_j$ = 125°C, $V_R$ = 200V, $dI/dt$ = 1A/ $\mu$ s, $dV_{DR}/dt$ = 20V/ $\mu$ s linear		400	750	μs
Qs	Stored charge	$I_T = 2000A$ , $T_j = 125$ °C, $dI/dt - 1A/\mu s$ ,		2700	6325	μC
lι	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	А
I <sub>H</sub>	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I <sub>T</sub> = 5A	-	300	mA





#### **GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol Parameter		Test Conditions	Max.	Units
$V_{GT}$	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
$V_{GD}$	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	400	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

## **CURVES**

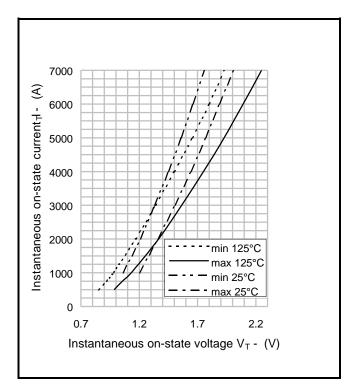


Fig.2 Maximum & minimum on-state characteristics

 $V_{TM}$  **EQUATION** Where

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$  B = -0.002455 C = 0.000096

 $M = A + Bin (I_T) + C.I_T + D. VI_T$  C = 0.000096D = 0.010486

these values are valid for  $T_j = 125$ °C for  $I_T 100$ A to 7000A

A = 0.722818

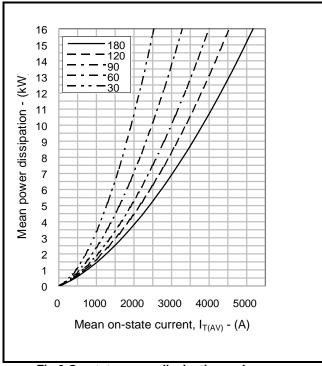


Fig.3 On-state power dissipation – sine wave

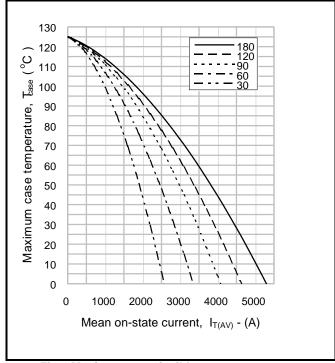


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

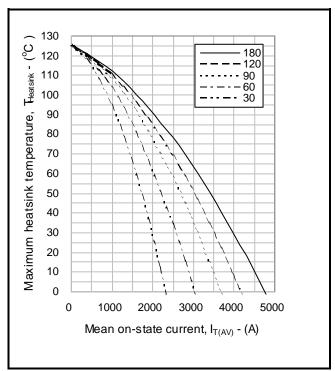


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

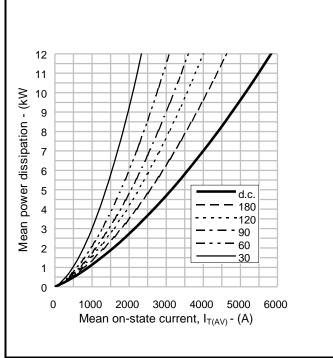
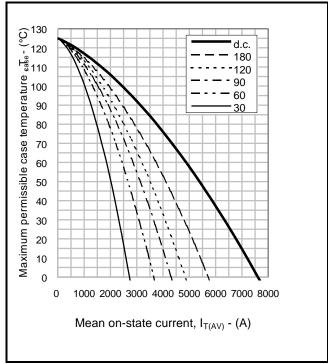
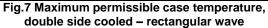


Fig.6 On-state power dissipation - rectangular wave







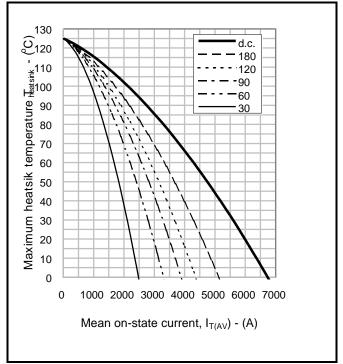
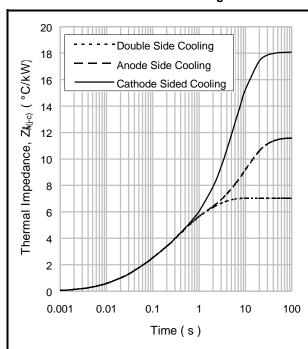


Fig.8 Maximum permissible heatsink temperature, double side cooled - rectangular wave



		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	0.502	1.333	2.9559	2.2335
	T <sub>i</sub> (s)	0.0137081	0.0548877	0.3311925	1.6905
Anode side cooled	R <sub>i</sub> (°C/kW)	1.3035	3.138	1.1859	5.9136
	T <sub>i</sub> (s)	0.0251065	0.2410256	1.0806	11.002
Cathode side cooled	R <sub>i</sub> (°C/kW)	1.2616	2.6216	13.3603	0.8304
	T <sub>i</sub> (s)	0.0245837	0.2005035	5.7854	16.765

 $Z_{th} = \sum [R_i x (1-exp. (t/t_i))]$ 

 $\Delta R_{\text{th(j-c)}}$  Conduction

Tables show the increments of thermal resistance  $R_{\text{th(j-c)}}$  when the device operates at conduction angles other than d.c.

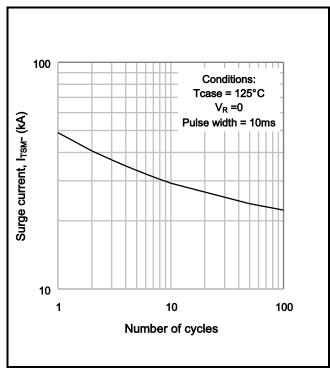
Double side cooling					
	$\Delta Z_{th}$ (	$\Delta Z_{th}(z)$			
θ°	sine.	rect.			
180	0.70	0.48			
120	0.80	0.68			
90	0.90	0.78			
60	1.00	0.89			
30	1.07	1.01			
15	1.10	1.07			

	Anode Side Cooling				Cathode Sided Cooling		
		$\Delta Z_{th}(z)$				$\Delta Z_{t}$	ı (z)
	θ°	sine.	rect.		θ°	sine.	rect.
	180	0.67	0.47		180	0.67	0.47
	120	0.77	0.66		120	0.77	0.66
	90	0.87	0.75		90	0.87	0.76
	60	0.95	0.86		60	0.95	0.86
	30	1.02	0.96	[	30	1.02	0.96
	15	1.05	1.02		15	1.05	1.02

Cathode Sided Cooling				
	$\Delta Z_{t}$	n (z)		
θ°	sine.	rect.		
180	0.67	0.47		
120	0.77	0.66		
90	0.87	0.76		
60	0.95	0.86		
30	1.02	0.96		

Fig.9 Maximum (limit) transient thermal impedance - junction to case (°C/kW)





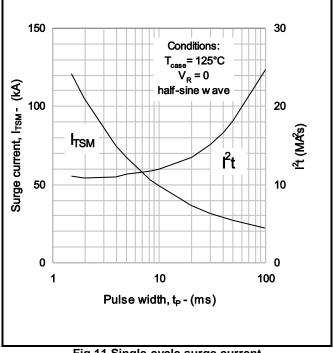
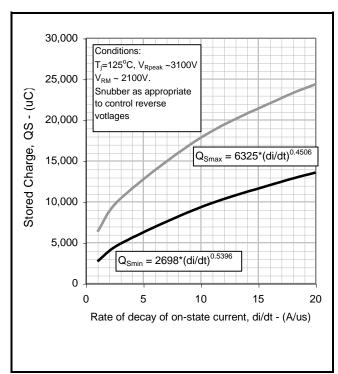
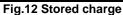


Fig.10 Multi-cycle surge current

Fig.11 Single-cycle surge current





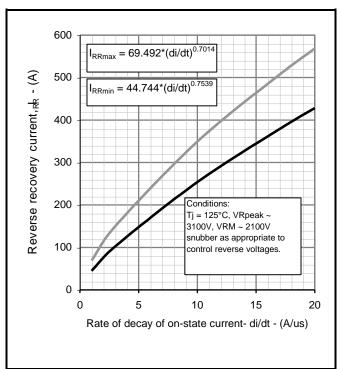


Fig.13 Reverse recovery current

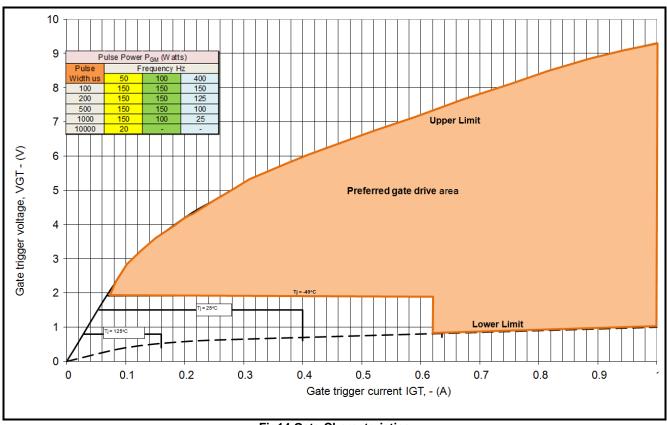


Fig14 Gate Characteristics

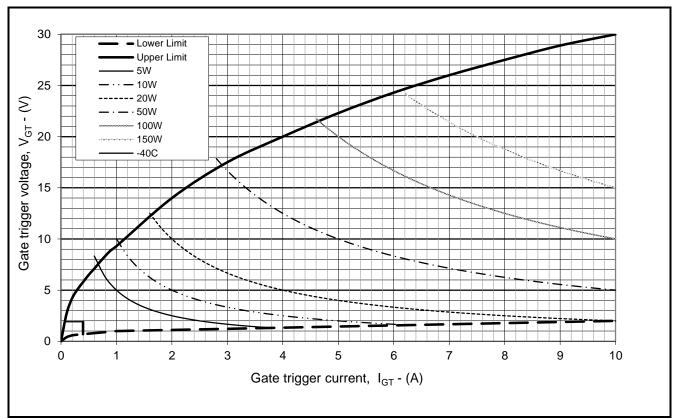


Fig. 15 Gate characteristics



#### **PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

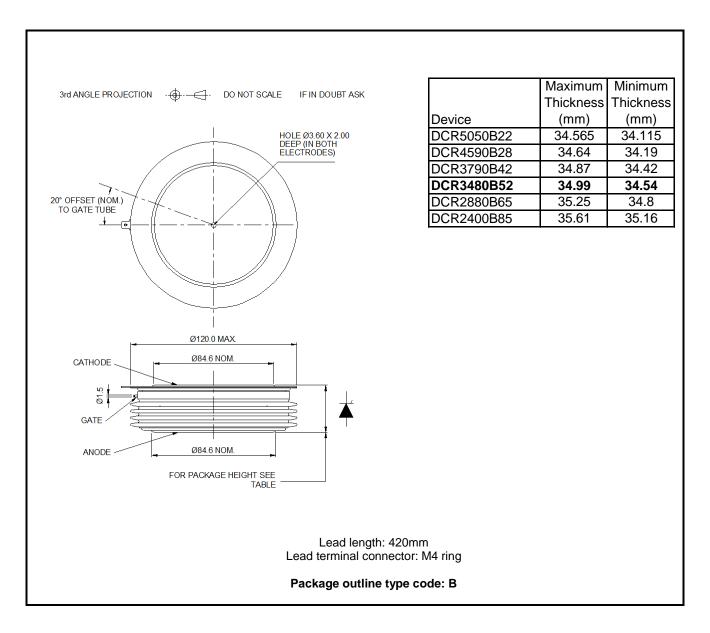


Fig.16 Package outline





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